

Takeshi Yoshimura

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5816257/publications.pdf>

Version: 2024-02-01

193
papers

2,308
citations

331259

21
h-index

301761

39
g-index

194
all docs

194
docs citations

194
times ranked

1737
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-layered assembly of vanadium pentoxide nanowires on graphene for nanowire-based lithography technique. <i>Nanotechnology</i> , 2022, 33, 075602.	1.3	0
2	Metallic Transport in Monolayer and Multilayer Molybdenum Disulfides by Molecular Surface Charge Transfer Doping. <i>ACS Applied Materials & Interfaces</i> , 2022, , .	4.0	3
3	Strong Photoluminescence Enhancement from Bilayer Molybdenum Disulfide via the Combination of UV Irradiation and Superacid Molecular Treatment. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 3530.	1.3	2
4	Ultralarge Photoluminescence Enhancement of Monolayer Molybdenum Disulfide by Spontaneous Superacid Nanolayer Formation. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 25280-25289.	4.0	8
5	Time-Dependent Imprint in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Ferroelectric Thin Films. <i>Advanced Electronic Materials</i> , 2021, 7, 2100151.	2.6	18
6	Correlation between photoluminescence and antiferromagnetic spin order in strongly correlated YMnO_3 ferroelectric epitaxial thin film. <i>AIP Advances</i> , 2021, 11, 075122.	0.6	1
7	Investigation of the wake-up process and time-dependent imprint of $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ film through the direct piezoelectric response. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	6
8	Good piezoelectricity of self-polarized thick epitaxial $(\text{K,Na})\text{NbO}_3$ films grown below the Curie temperature (240°C) using a hydrothermal method. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	8
9	Investigation of the electrocaloric effect in ferroelectric polymer film through direct measurement under alternating electric field. <i>Applied Physics Express</i> , 2020, 13, 041007.	1.1	5
10	Photoactivation of Strong Photoluminescence in Superacid-Treated Monolayer Molybdenum Disulfide. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 36496-36504.	4.0	24
11	Change in the defect structure of composition controlled single-phase YbFe_2O_4 epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPB07.	0.8	4
12	Investigation of efficient piezoelectric energy harvesting from impulsive force. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPD04.	0.8	6
13	Supersensitive Ultrasound Probes for Medical Imaging by Piezoelectric MEMS with Complemented Transmitting and Receiving Transducers. , 2020, , .		2
14	Novel Ferroelectric Gate Field-Effect Transistors (FeFETs); Controlled Polarization-Type FeFETs. <i>Topics in Applied Physics</i> , 2020, , 147-174.	0.4	0
15	Fabrication and Characterization of $(\text{Ba,Lu})\text{SnO}_3$ Semiconducting Epitaxial Films on (111) and (001) SrTiO_3 Substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1700800.	0.8	2
16	Convection-Assisted Preparation of a Strong Electron Dopant, Benzyl Viologen, for Surface-Charge Transfer Doping of Molybdenum Disulfide. <i>ChemistryOpen</i> , 2019, 8, 908-914.	0.9	6
17	The effects of small amounts of oxygen during deposition on structural changes in sputtered HfO_2 -based films. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLB03.	0.8	8
18	Fabrication of chemical composition controlled YbFe_2O_4 epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLB11.	0.8	1

#	ARTICLE	IF	CITATIONS
19	Piezoelectric energy harvesting from AC current-carrying wire. Japanese Journal of Applied Physics, 2019, 58, SLLD10.	0.8	10
20	Microenergy harvesting using BiFeO ₃ films. , 2019, , 195-215.		2
21	Electromechanical characteristics of piezoelectric vibration energy harvester with 2-degree-of-freedom system. Applied Physics Letters, 2019, 114, .	1.5	15
22	Electronic Structure Mosaicity of Monolayer Transition Metal Dichalcogenides by Spontaneous Pattern Formation of Donor Molecules. ACS Applied Materials & Interfaces, 2019, 11, 15922-15926.	4.0	3
23	Solvent engineering for strong photoluminescence enhancement of monolayer molybdenum disulfide in redox-active molecular treatment. Applied Physics Express, 2019, 12, 051014.	1.1	5
24	Time-resolved simulation of the negative capacitance stage emerging at the ferroelectric/semiconductor hetero-junction. AIP Advances, 2019, 9, 025037.	0.6	3
25	Demonstration of high-performance piezoelectric MEMS vibration energy harvester using BiFeO ₃ film with improved electromechanical coupling factor. Sensors and Actuators A: Physical, 2019, 291, 167-173.	2.0	19
26	Saturated and Pinched Ferroelectric Hysteresis Loops in BiFeO ₃ Ceramics. Journal of the Korean Physical Society, 2019, 74, 269-273.	0.3	0
27	Quantitative analysis of the direct piezoelectric response of bismuth ferrite films by scanning probe microscopy. Scientific Reports, 2019, 9, 19727.	1.6	4
28	Output Power of Piezoelectric MEMS Vibration Energy Harvesters Under Random Oscillation. Journal of Physics: Conference Series, 2019, 1407, 012082.	0.3	0
29	Monolithic Integration of P(VDF-TrFE) Thin Film on CMOS for Wide-band Ultrasonic Transducer Arrays. , 2019, , .		4
30	The effect of crystal distortion and domain structure on piezoelectric properties of BiFeO ₃ thin films. Japanese Journal of Applied Physics, 2018, 57, 11UF07.	0.8	5
31	Investigation of piezoelectric energy harvesting from human walking. Journal of Physics: Conference Series, 2018, 1052, 012113.	0.3	2
32	Fabrication of Y Doped HfO ₂ Epitaxial Films Directly on (001) Si Substrate. Zairyo/Journal of the Society of Materials Science, Japan, 2018, 67, 844-848.	0.1	0
33	Characterization of piezoelectric MEMS vibration energy harvesters using random vibration. Japanese Journal of Applied Physics, 2018, 57, 11UD10.	0.8	2
34	Direct piezoelectric properties of BiFeO ₃ epitaxial films grown by combinatorial sputtering. Journal of Physics: Conference Series, 2018, 1052, 012020.	0.3	5
35	Investigation of mechanical nonlinear effect in piezoelectric MEMS vibration energy harvesters. Japanese Journal of Applied Physics, 2018, 57, 11UD03.	0.8	9
36	Direct piezoelectric response in vinylidene fluoride-trifluoroethylene copolymer films. Japanese Journal of Applied Physics, 2018, 57, 11UG01.	0.8	0

#	ARTICLE	IF	CITATIONS
37	Tuning Transition-Metal Dichalcogenide Field-Effect Transistors by Spontaneous Pattern Formation of an Ultrathin Molecular Dopant Film. ACS Nano, 2018, 12, 10123-10129.	7.3	3
38	Systematic Study of Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Acid Treatment. Langmuir, 2018, 34, 10243-10249.	1.6	29
39	Reaction of N,N-dimethylformamide and divalent viologen molecule to generate an organic dopant for molybdenum disulfide. AIP Advances, 2018, 8, 055313.	0.6	4
40	Cerium ion doping into self-assembled Ge using three-dimensional dot structure. Journal of Crystal Growth, 2017, 468, 696-700.	0.7	1
41	Photoelectron spectroscopic study on monolayer pentacene thin-film/polar ZnO single-crystal hybrid interface. Applied Physics Express, 2017, 10, 025702.	1.1	5
42	High efficiency piezoelectric MEMS vibrational energy harvesters using (100) oriented BIFEO ₃ films. , 2017, , .		1
43	Growth and ferroelectric properties of La and Al codoped BiFeO ₃ epitaxial films. Journal of Applied Physics, 2017, 121, 174102.	1.1	7
44	Crystallographic polarity effect of ZnO on thin film growth of pentacene. Japanese Journal of Applied Physics, 2017, 56, 04CJ03.	0.8	4
45	Control of native acceptor density in epitaxial Cu ₂ O thin films grown by electrochemical deposition. Journal of Crystal Growth, 2017, 468, 245-248.	0.7	7
46	Fabrication and electrical properties of a (Pb,La)(Zr,Ti)O ₃ capacitor with pulsed laser deposited Sn-doped In ₂ O ₃ bottom electrode on Al ₂ O ₃ (0001). Japanese Journal of Applied Physics, 2017, 56, 07KC02.	0.8	2
47	Development of piezoelectric bistable energy harvester based on buckled beam with axially constrained end condition for human motion. Japanese Journal of Applied Physics, 2017, 56, 10PD02.	0.8	12
48	Origin of the photoinduced current of strongly correlated YMnO ₃ ferroelectric epitaxial films. Japanese Journal of Applied Physics, 2017, 56, 10PB08.	0.8	2
49	Large enhancement of positive magnetoresistance by Ce doping in Si epitaxial thin films. Applied Physics Letters, 2016, 109, 112101.	1.5	0
50	Comparative study of ferroelectric (K,Na)NbO ₃ thin films pulsed laser deposition on platinum substrates with different orientation. , 2016, , .		0
51	Novel chemical vapor deposition process of ZnO films using nonequilibrium N ₂ plasma generated near atmospheric pressure with small amount of O ₂ below 1%. Journal of Applied Physics, 2016, 119, 175302.	1.1	3
52	Al:ZnO top electrodes deposited with various oxygen pressures for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors. Electronics Letters, 2016, 52, 230-232.	0.5	5
53	Reliability of the Properties of (Pb,La)(Zr,Ti)O ₃ Capacitors with Non-noble Metal Oxide Electrodes stored in an H ₂ Atmosphere. MRS Advances, 2016, 1, 369-374.	0.5	3
54	Low temperature formation of highly resistive ZnO films using nonequilibrium N ₂ /O ₂ plasma generated near atmospheric pressure. Thin Solid Films, 2016, 616, 415-418.	0.8	1

#	ARTICLE	IF	CITATIONS
55	Novel Ferroelectric-Gate Field-Effect Thin Film Transistors (FeTFTs): Controlled Polarization-Type FeTFTs. Topics in Applied Physics, 2016, , 111-138.	0.4	0
56	Direct measurements of electrocaloric effect in ferroelectrics using thin-film thermocouples. Japanese Journal of Applied Physics, 2016, 55, 10TB04.	0.8	7
57	Thickness dependence of piezoelectric properties of BiFeO ₃ films fabricated using rf magnetron sputtering system. Japanese Journal of Applied Physics, 2016, 55, 10TA16.	0.8	19
58	Effects of (Bi ^{1/2} ,Na ^{1/2})TiO ₃ on the electrical properties of BiFeO ₃ -based thin films. Japanese Journal of Applied Physics, 2016, 55, 10TA17.	0.8	0
59	Fabrication of doped Pb(Zr,Ti)O ₃ capacitors on Pt substrates with different orientations. Electronics Letters, 2016, 52, 1399-1401.	0.5	0
60	Comparative Study of Hydrogen- and Deuterium-Induced Degradation of Ferroelectric (Pb,La)(Zr,Ti)O ₃ Capacitors Using Time-of-Flight Secondary Ion Measurement. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2016, 63, 1668-1673.	1.7	6
61	Low-voltage operation of Si-based ferroelectric field effect transistors using organic ferroelectrics, poly(vinylidene fluoride-trifluoroethylene), as a gate dielectric. Japanese Journal of Applied Physics, 2016, 55, 04EE04.	0.8	5
62	Lowering the growth temperature of strongly-correlated YbFe ₂ O ₄ thin films prepared by pulsed laser deposition. Thin Solid Films, 2016, 614, 44-46.	0.8	9
63	Ferroelectric properties of (Pb,La)(Zr,Ti)O ₃ capacitors employing Al-doped ZnO top electrodes prepared by pulsed laser deposition under different oxygen pressures. Japanese Journal of Applied Physics, 2016, 55, 06JB04.	0.8	0
64	The effect of H ₂ distribution in (Pb,La)(Zr,Ti)O ₃ capacitors with conductive oxide electrodes on the degradation of ferroelectric properties. Materials Research Society Symposia Proceedings, 2015, 1729, 93-98.	0.1	0
65	Effects of polarization of polar semiconductor on electrical properties of poly(vinylidene Tj ETQq1 1 0.784314 rgBT _{1,1} Overlock 10 Tf 50	1.1	1
66	Effect of Al-doped ZnO or Sn-doped In ₂ O ₃ electrode on ferroelectric properties of (Pb,La)(Zr,Ti)O ₃ capacitors. Japanese Journal of Applied Physics, 2015, 54, 05ED03.	0.8	7
67	Hydrogen profile measurement of (Pb,La)(Zr,Ti)O ₃ capacitor with conductive electrode after hydrogen annealing. , 2015, , .		1
68	Growth and characterization of (1-x)BiFeO ₃ -x(Bi _{0.5} ,K _{0.5})TiO ₃ thin films. Japanese Journal of Applied Physics, 2015, 54, 10NA14.	0.8	1
69	Theoretical analysis of linear and nonlinear piezoelectric vibrational energy harvesters for human walking. Japanese Journal of Applied Physics, 2015, 54, 10ND02.	0.8	5
70	Evaluation of the electronic states in highly Ce doped Si films grown by low temperature molecular beam epitaxy system. Journal of Crystal Growth, 2015, 425, 158-161.	0.7	7
71	Effect of excess Pb on ferroelectric characteristics of conductive Al-doped ZnO and Sn-doped In ₂ O ₃ top electrodes in PbLaZrTiO _x capacitors. International Journal of Materials Research, 2015, 106, 83-87.	0.1	6
72	Improved reliability properties of (Pb,La)(Zr,Ti)O ₃ ferroelectric capacitors by thin aluminium-doped zinc oxide buffer layer. Electronics Letters, 2014, 50, 799-801.	0.5	4

#	ARTICLE	IF	CITATIONS
73	Output power of piezoelectric MEMS vibration energy harvesters under random oscillations. Journal of Physics: Conference Series, 2014, 557, 012101.	0.3	3
74	Correlation between the intra-atomic Mn ³⁺ photoluminescence and antiferromagnetic transition in an YMnO ₃ epitaxial film. Applied Physics Express, 2014, 7, 023002.	1.1	10
75	Enhancement of piezoelectric properties of (100)-orientated BiFeO ₃ films on (100)LaNiO ₃ /Si. Japanese Journal of Applied Physics, 2014, 53, 09PA14.	0.8	19
76	Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O ₃ capacitors: effect of oxide insulator encapsulation and oxide buffer layer. Journal of Materials Science: Materials in Electronics, 2014, 25, 2155-2161.	1.1	5
77	Near-surface structure of polar ZnO surfaces prepared by pulsed laser deposition. Thin Solid Films, 2014, 559, 88-91.	0.8	4
78	Crystal structure and local piezoelectric properties of strain-controlled (001) BiFeO ₃ epitaxial thin films. Thin Solid Films, 2014, 550, 738-741.	0.8	8
79	Piezoelectric properties of (100) orientated BiFeO ₃ thin films on LaNiO ₃ . Japanese Journal of Applied Physics, 2014, 53, 08NB02.	0.8	11
80	Effect of the annealing temperature of P(VDF/TrFE) thin films on their ferroelectric properties. Journal of the Korean Physical Society, 2013, 62, 1065-1068.	0.3	6
81	Comparative study of electrical properties of PbLaZrTiOx capacitors with Al-doped ZnO and ITO top electrodes. , 2013, , .		0
82	Electrical properties of PbLaZrTiOx capacitors with conductive oxide buffer layer on Pt electrodes. , 2013, , .		0
83	Piezoelectric Vibrational Energy Harvester Using Lead-Free Ferroelectric BiFeO ₃ Films. Applied Physics Express, 2013, 6, 051501.	1.1	37
84	Effects of La substitution for BiFeO ₃ epitaxial thin films. Journal of the Korean Physical Society, 2013, 62, 1069-1072.	0.3	2
85	Orientation Control of ZnO Films Deposited Using Nonequilibrium Atmospheric Pressure N ₂ /O ₂ Plasma. Japanese Journal of Applied Physics, 2013, 52, 01AC03.	0.8	4
86	Electrical Properties of Sol-Gel Derived PbLaZrTiOx Capacitors with Nonnoble Metal Oxide Top Electrodes. ECS Transactions, 2013, 50, 43-48.	0.3	4
87	Development of Piezoelectric MEMS Vibration Energy Harvester Using (100) Oriented BiFeO ₃ Ferroelectric Film. Journal of Physics: Conference Series, 2013, 476, 012007.	0.3	19
88	Enhancement of Direct Piezoelectric Properties of Domain-Engineered (100) BiFeO ₃ Films. Japanese Journal of Applied Physics, 2013, 52, 09KA03.	0.8	10
89	Effect of Target Surface Microstructure on Morphological and Electrical Properties of Pulsed-Laser-Deposited BiFeO ₃ Epitaxial Thin Films. Japanese Journal of Applied Physics, 2013, 52, 045803.	0.8	5
90	Fabrication and Electric Properties of Ferroelectric-Gate Thin Film Transistors with Nano-Channel. Journal of the Vacuum Society of Japan, 2013, 56, 172-175.	0.3	0

#	ARTICLE	IF	CITATIONS
91	Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. Japanese Journal of Applied Physics, 2012, 51, 09LB04.	0.8	8
92	Investigation of Gas Sensing Characteristics of TiO ₂ Nanotube Field-Effect Transistor. Japanese Journal of Applied Physics, 2012, 51, 11PE10.	0.8	4
93	Growth temperature and thickness dependences of crystal and micro domain structures of BiFeO ₃ epitaxial films. , 2012, , .		0
94	Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01.	0.8	1
95	Electronic Transport in Organic Ferroelectric Gate Field-Effect Transistors with ZnO Channel. Materials Research Society Symposia Proceedings, 2012, 1430, 19.	0.1	1
96	Direct piezoelectric properties of (100) and (111) BiFeO ₃ epitaxial thin films. Applied Physics Letters, 2012, 100, 102901.	1.5	69
97	Low Temperature Growth of ZnO Thin Films by Non-Equilibrium Atmospheric Pressure N ₂ /O ₂ Plasma and the Growth Morphology of the Films. Zairyo/Journal of the Society of Materials Science, Japan, 2012, 61, 756-759.	0.1	5
98	Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. Japanese Journal of Applied Physics, 2012, 51, 09LB04.	0.8	5
99	Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01.	0.8	6
100	Characterization of Direct Piezoelectric Effect in 31 and 33 Modes for Application to Vibration Energy Harvester. Japanese Journal of Applied Physics, 2011, 50, 09ND17.	0.8	8
101	Characterization of Direct Piezoelectric Properties for Vibration Energy Harvesting. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092026.	0.3	9
102	Surface preparation of ZnO single-crystal substrate for the epitaxial growth of ZnO thin films. Journal of Crystal Growth, 2011, 318, 516-518.	0.7	7
103	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	0.8	6
104	Effect of Ferroelectric Polarization Domain Structure on Electronic Transport Property of Ferroelectric/ZnO Heterostructure. Japanese Journal of Applied Physics, 2011, 50, 09NA06.	0.8	5
105	Effect of Lattice Misfit Strain on Crystal System and Ferroelectric Property of BiFeO ₃ Epitaxial Thin Films. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092064.	0.3	1
106	Fabrication of robust PbLa(Zr,Ti)O ₃ capacitor structures using insulating oxide encapsulation layers for FeRAM integration. Electronics Letters, 2011, 47, 486.	0.5	2
107	Electronic Transport Property of a YbMnO ₃ /ZnO Heterostructure. Journal of the Korean Physical Society, 2011, 58, 792-796.	0.3	6
108	Direct Piezoelectricity of PZT Films and Application to Vibration Energy Harvesting. Journal of the Korean Physical Society, 2011, 59, 2524-2527.	0.3	9

#	ARTICLE	IF	CITATIONS
109	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	0.8	14
110	Effect of Ferroelectric Polarization Domain Structure on Electronic Transport Property of Ferroelectric/ZnO Heterostructure. Japanese Journal of Applied Physics, 2011, 50, 09NA06.	0.8	14
111	Characterization of Direct Piezoelectric Effect in 31 and 33 Modes for Application to Vibration Energy Harvester. Japanese Journal of Applied Physics, 2011, 50, 09ND17.	0.8	4
112	Fine-structured ZnO patterns with sub-micrometer on the ceramic surface fabricated by a replication method. Journal of the Ceramic Society of Japan, 2010, 118, 1140-1143.	0.5	4
113	Fine-structured patterns of porous alumina material fabricated by a replication method. Journal of the European Ceramic Society, 2010, 30, 2735-2739.	2.8	10
114	Control of carrier concentration of p-type transparent conducting CuScO ₂ (0001) epitaxial films. Thin Solid Films, 2010, 518, 3097-3100.	0.8	5
115	Growth process observation of homoepitaxial ZnO thin films using optical emission spectra during pulsed laser deposition. Thin Solid Films, 2010, 518, 2971-2974.	0.8	8
116	Analysis of carrier modulation in channel of ferroelectric-gate transistors having polar semiconductor. Thin Solid Films, 2010, 518, 3026-3029.	0.8	14
117	Control of cathodic potential for deposition of ZnO by constant-current electrochemical method. Thin Solid Films, 2010, 518, 2957-2960.	0.8	10
118	Direct Piezoelectric Properties of Mn-Doped ZnO Epitaxial Films. Japanese Journal of Applied Physics, 2010, 49, 021501.	0.8	25
119	Ferroelectric Properties of Magnetoferroelectric YMnO ₃ Epitaxial Films at around the Neel Temperature. Key Engineering Materials, 2010, 445, 144-147.	0.4	1
120	Local Piezoelectric and Conduction Properties of BiFeO ₃ Epitaxial Thin Films. Japanese Journal of Applied Physics, 2010, 49, 09MB02.	0.8	11
121	Electron transport properties of Zn _{0.88} Mn _{0.12} O ⁺ ZnO modulation-doped heterostructures. Journal of Vacuum Science & Technology B, 2009, 27, 1760.	1.3	6
122	Magnetic Properties of Uniformly Ce-Doped Si Thin Films with n-Type Conduction. Japanese Journal of Applied Physics, 2009, 48, 033003.	0.8	7
123	Polarization Switching Behavior of YMnO ₃ Thin Film at around Magnetic Phase Transition Temperature. Japanese Journal of Applied Physics, 2009, 48, 09KB05.	0.8	12
124	Spin-phonon coupling in multiferroic YbMnO ₃ studied by Raman scattering. Journal of Physics Condensed Matter, 2009, 21, 064218.	0.7	18
125	Effects of Mg doping on structural, optical, and electrical properties of CuScO ₂ (0001) epitaxial films. Vacuum, 2009, 84, 618-621.	1.6	11
126	Optical and electrical properties of CuScO ₂ epitaxial films prepared by combining two-step deposition and post-annealing techniques. Journal of Crystal Growth, 2009, 311, 1117-1122.	0.7	17

#	ARTICLE	IF	CITATIONS
127	Contribution of s-d exchange interaction to magnetoresistance of ZnO-based heterostructures with a magnetic barrier. <i>Physical Review B</i> , 2009, 80, .	1.1	10
128	Fabrication of the fine structured alumina materials with nanoimprint method. <i>Journal of the Ceramic Society of Japan</i> , 2009, 117, 534-536.	0.5	4
129	Dielectric properties of ferroelectric/DMS heterointerface using YMnO ₃ and Ce doped Si. <i>Applied Surface Science</i> , 2008, 254, 6218-6221.	3.1	5
130	Effects of spontaneous and piezoelectric polarizations on carrier confinement at the Zn _{0.88} Mn _{0.12} O/ZnO interface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3107-3109.	0.8	3
131	Electro-optic property of ZnO:Mn epitaxial films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3110-3112.	0.8	1
132	Electrical and optical properties of excess oxygen intercalated CuScO ₂ (0001) epitaxial films prepared by oxygen radical annealing. <i>Thin Solid Films</i> , 2008, 516, 5785-5789.	0.8	11
133	Effect of electrically degenerated layer on the carrier transport property of ZnO epitaxial thin films. <i>Applied Surface Science</i> , 2008, 254, 6248-6251.	3.1	13
134	Influence of antiferromagnetic exchange interaction on magnetic properties of ZnMnO thin films grown pseudomorphically on ZnO (0001Å ⁻¹) single-crystal substrates. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	33
135	Magnetic and dielectric properties of Yb(Mn _{1-x} Al _x)O ₃ thin films. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2008, 55, 1056-1060.	1.7	2
136	Effect of Mn doping on the electric and dielectric properties of ZnO epitaxial films. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	21
137	CaBi ₄ Ti ₄ O ₁₅ thin film deposition on electroplated Platinum substrates using a sol-gel method. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1113, 1.	0.1	0
138	Effects of Oxygen Annealing on Dielectric Properties of LuFeCuO ₄ . <i>Japanese Journal of Applied Physics</i> , 2008, 47, 8464.	0.8	12
139	Electrical Characteristics of Controlled-Polarization-Type Ferroelectric-Gate Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 8874.	0.8	35
140	Spin-dependent transport in a ZnMnO ₂ •ZnO heterostructure. <i>Journal of Applied Physics</i> , 2008, 103, 07D124.	1.1	7
141	Influence of antiferromagnetic ordering on ferroelectric polarization switching of YMnO ₃ /epitaxial thin films. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2007, 54, 2641-2644.	1.7	6
142	The comparison of the growth models of silicon nitride ultrathin films fabricated using atmospheric pressure plasma and radio frequency plasma. <i>Journal of Applied Physics</i> , 2007, 101, 023513.	1.1	6
143	Magnetic and Dielectric Properties of Yb(Mn ^{1-x} Al ^x)O ₃ Thin Films. <i>Applications of Ferroelectrics, IEEE International Symposium on</i> , 2007, , .	0.0	0
144	Spin-coupled phonons in multiferroic YbMnO ₃ epitaxial films by Raman scattering. <i>Journal of Physics: Conference Series</i> , 2007, 92, 012126.	0.3	12

#	ARTICLE	IF	CITATIONS
145	Magnetic frustration behavior of ferroelectric ferromagnet YbMnO ₃ epitaxial films. Journal of Applied Physics, 2007, 101, 09M107.	1.1	12
146	Multiferroic behaviour of YMnO ₃ and YbMnO ₃ epitaxial films. Philosophical Magazine Letters, 2007, 87, 193-201.	0.5	20
147	Influence of Antiferromagnetic Ordering on Ferroelectric Polarization Switching of YMnO ₃ Epitaxial Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
148	Raman scattering studies on multiferroic YMnO ₃ . Journal of Physics Condensed Matter, 2007, 19, 365239.	0.7	55
149	Magnetic properties of low-temperature grown Si:Ce thin films on (001) Si substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e726-e728.	1.0	10
150	Effect of Bi substitution on the magnetic and dielectric properties of epitaxially grown BaFe _{0.3} Zr _{0.7} O ₃ thin films on SrTiO ₃ substrates. Journal of Physics and Chemistry of Solids, 2007, 68, 1515-1521.	1.9	1
151	Preparation and the magnetic property of ZnMnO thin films on ZnO single crystal substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e711-e713.	1.0	15
152	Growth and Ferromagnetic Properties of Ferroelectric YbMnO ₃ Thin Films. Japanese Journal of Applied Physics, 2006, 45, 7329-7331.	0.8	12
153	Reaction of Si with excited nitrogen species in pure nitrogen plasma near atmospheric pressure. Thin Solid Films, 2006, 506-507, 423-426.	0.8	16
154	Effect of Additional Oxygen on Formation of Silicon Oxynitride Using Nitrogen Plasma Generated near Atmospheric Pressure. Japanese Journal of Applied Physics, 2006, 45, 9025-9028.	0.8	6
155	Single-Wall Carbon Nanotube Field Effect Transistors with Non-Volatile Memory Operation. Japanese Journal of Applied Physics, 2006, 45, L1036-L1038.	0.8	20
156	Novel Ferroelectric Gate Thin-Film Transistors Using a Polar Semiconductor Channel. Japanese Journal of Applied Physics, 2006, 45, L1266-L1269.	0.8	5
157	Detailed structural analysis and dielectric properties of silicon nitride film fabricated using pure nitrogen plasma generated near atmospheric pressure. Journal of Applied Physics, 2006, 100, 073710.	1.1	14
158	Low-Temperature Growth and Characterization of Epitaxial YMnO ₃ /Y ₂ O ₃ /Si MFIS Capacitors with Thinner Insulator Layer. Japanese Journal of Applied Physics, 2005, 44, 6977-6980.	0.8	8
159	Epitaxial growth of CuScO ₂ thin films on sapphire a-plane substrates by pulsed laser deposition. Journal of Applied Physics, 2005, 97, 083535.	1.1	25
160	Formation of Silicon Oxynitride Films with Low Leakage Current Using N ₂ /O ₂ Plasma near Atmospheric Pressure. Japanese Journal of Applied Physics, 2004, 43, 7853-7856.	0.8	7
161	Pulsed-Laser-Deposited YMnO ₃ Epitaxial Films with Square Polarization-Electric Field Hysteresis Loop and Low-Temperature Growth. Japanese Journal of Applied Physics, 2004, 43, 6613-6616.	0.8	31
162	Synthesis of Bi(FexAl _{1-x})O ₃ Thin Films by Pulsed Laser Deposition and Its Structural Characterization. Japanese Journal of Applied Physics, 2004, 43, 6609-6612.	0.8	13

#	ARTICLE	IF	CITATIONS
163	Fabrication of Silicon Nitride Film using Pure Nitrogen Plasma Generated near Atmospheric Pressure for III-V Semiconductor Fabrication. Materials Research Society Symposia Proceedings, 2004, 831, 144.	0.1	0
164	P-E Measurements for Ferroelectric Gate Capacitors. Integrated Ferroelectrics, 2004, 61, 59-64.	0.3	0
165	Analysis of nitrogen plasma generated by a pulsed plasma system near atmospheric pressure. Journal of Applied Physics, 2004, 96, 6094-6096.	1.1	19
166	Polarization Hysteresis Loops of Ferroelectric Gate Capacitors Measured by Sawyer-Tower Circuit. Japanese Journal of Applied Physics, 2003, 42, 6011-6014.	0.8	13
167	Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 784, 971.	0.1	0
168	Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 786, 971.	0.1	0
169	Ferromagnetic and ferroelectric behaviors of A-site substituted YMnO ₃ -based epitaxial thin films. Journal of Applied Physics, 2003, 93, 6990-6992.	1.1	44
170	Influence of Schottky and Poole-Frenkel emission on the retention property of YMnO ₃ -based metal/ferroelectric/insulator/semiconductor capacitors. Journal of Applied Physics, 2003, 94, 4036-4041.	1.1	34
171	Dielectric and transverse piezoelectric properties of sol-gel-derived (001) Pb[Yb _{1/2} Nb _{1/2}]O ₃ -PbTiO ₃ epitaxial thin films. Applied Physics Letters, 2003, 82, 4767-4769.	1.5	19
172	Ferroelectric properties of YMnO ₃ epitaxial films for ferroelectric-gate field-effect transistors. Journal of Applied Physics, 2003, 93, 5563-5567.	1.1	105
173	Improvement of Surface Morphology and Dielectric Property of YMnO ₃ Films. Japanese Journal of Applied Physics, 2003, 42, 6003-6006.	0.8	4
174	Growth and properties of (001) BiScO ₃ -PbTiO ₃ epitaxial films. Applied Physics Letters, 2002, 81, 2065-2066.	1.5	54
175	Growth and piezoelectric properties of Pb(Yb _{1/2} Nb _{1/2})O ₃ -PbTiO ₃ epitaxial films. Journal of Applied Physics, 2002, 92, 3979-3984.	1.1	23
176	Phase Development and Electrical Properties of Pb(Yb _{1/2} Nb _{1/2})O ₃ -PbTiO ₃ Epitaxial Films. Integrated Ferroelectrics, 2002, 50, 33-42.	0.3	5
177	Transverse piezoelectric properties of epitaxial Pb(Yb _{1/2} Nb _{1/2})O ₃ -PbTiO ₃ (50/50) films. Journal of Crystal Growth, 2001, 229, 445-449.	0.7	22
178	Improvement of Y ₂ O ₃ /Si interface for FeRAM application. Applied Surface Science, 2000, 159-160, 138-142.	3.1	14
179	Characterization of ferroelectricity in metal/ferroelectric/insulator/semiconductor structure by pulsed C-V measurement; Ferroelectricity in YMnO ₃ /Y ₂ O ₃ /Si structure. Journal of Applied Physics, 2000, 87, 3444-3449.	1.1	72
180	YMnO ₃ and YbMnO ₃ Thin Films for fet type FeRam Application. Materials Research Society Symposia Proceedings, 1999, 574, 237.	0.1	3

#	ARTICLE	IF	CITATIONS
181	Detailed C-V Analysis for YbMnO ₃ /Y ₂ O ₃ /Si Structure. Materials Research Society Symposia Proceedings, 1999, 574, 359.	0.1	1
182	Evaluation of Ferroelectricity in MFIS Type Capacitor Using Pulsed C-V Measurements. Materials Research Society Symposia Proceedings, 1999, 596, 407.	0.1	0
183	Effects of Stoichiometry and A-site Substitution on the Electrical Properties of Ferroelectric YMnO ₃ . Japanese Journal of Applied Physics, 1998, 37, 5280-5284.	0.8	17
184	Ferroelectric properties of c-oriented YMnO ₃ films deposited on Si substrates. Applied Physics Letters, 1998, 73, 414-416.	1.5	60
185	YMnO ₃ Thin Films Prepared from Solutions for Non Volatile Memory Devices. Japanese Journal of Applied Physics, 1997, 36, L1601-L1603.	0.8	41
186	Fabrication of YMnO ₃ Thin Films on Si Substrates by a Pulsed Laser Deposition Method. Japanese Journal of Applied Physics, 1997, 36, 5921-5924.	0.8	21
187	Formation of YMnO ₃ films directly on Si substrate. Journal of Crystal Growth, 1997, 174, 796-800.	0.7	11
188	The initial stage of BaTiO ₃ epitaxial films on etched and annealed SrTiO ₃ substrates. Journal of Crystal Growth, 1997, 174, 790-795.	0.7	24
189	Fabrication of YMnO ₃ Films: New Candidate for Non-Volatile Memory Devices. Materials Research Society Symposia Proceedings, 1996, 433, 119.	0.1	0
190	Epitaxially grown YMnO ₃ film: New candidate for nonvolatile memory devices. Applied Physics Letters, 1996, 69, 1011-1013.	1.5	303
191	Growth mechanism of YMnO ₃ film as a new candidate for nonvolatile memory devices. Journal of Applied Physics, 1996, 80, 7084-7088.	1.1	94
192	Dielectric Behavior of YMnO ₃ ; Epitaxial Thin Film at around Magnetic Phase Transition Temperature. Advances in Science and Technology, 0, , .	0.2	0
193	Fabrication and Magneto-Transport Properties of Zn _{0.88-x} Mg _x Mn _{0.12} O/ZnO Heterostructures Grown on ZnO Single-Crystal Substrates. Advances in Science and Technology, 0, , .	0.2	0